## NSN 5962-01-351-9521

Memory Microcircuit - Page 1 of 2

Between 0.220 inches and 0.310 inches

Overall Height: 0.400 inches Body Length: 1.280 inches Body Width:



View Online at https://aerobasegroup.com/nsn/5962-01-351-9521

Between 0.140 inches and 0.185 inches  Maximum Power Dissipation Rating:  1.2 watts  Operating Tempurature Range: -65.0/+125.0 degrees celsius  Storage Tempurature Range: -65.0/+150.0 degrees celsius  End Application:  Satellite communications terminal an/usc-3 (v) 1 Features Provided: Hermetically sealed and burn in and monolithic and programmed Inclosure Material: Ceramic Inclosure Configuration:  Dual-in-line Output Logic Form: Transistor-transistor logic Input Circuit Pattern: 20 input Case Outline Source And Designator: D-9 mil-m-38510  Current Rating Per Characteristic: 165.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 12.0 volts power source Time Rating Per Chacteristic: 35.00 nanoseconds delay Memory Device Type: Pal Test Data Document:	Body Height:
1.2 watts  Operating Tempurature Range: -55.0/+125.0 degrees celsius  Storage Tempurature Range: -65.0/+125.0 degrees celsius  End Application: Satellite communications terminal an/usc-3 (v) 1  Features Provided: Hermetically sealed and burn in and monolithic and programmed Inclosure Material: Ceramic Inclosure Material: Ceramic Inclosure Configuration: Dual-in-line Output Logic Form: Transistor-transistor logic Input Circuit Pattern: 20 input Case Outline Source And Designator: D-9 mil-m-38510  Current Rating Per Characteristic: 165.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 12.0 volts power source Time Rating Per Characteristic: 35.00 nanoseconds delay Memory Device Type: Pal Test Data Document:	Between 0.140 inches and 0.185 inches
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Storage Tempurature Range: -65.0/+125.0 degrees celsius  End Application: Satellite communications terminal an/usc-3 (v) 1 Features Provided: Hermetically sealed and burn in and monolithic and programmed Inclosure Material: Ceramic Inclosure Configuration: Dual-in-line Output Logic Form: Transistor-transistor logic Input Circuit Pattern: 20 input Case Outline Source And Designator: D-9 mil-m-38510 Current Rating Per Characteristic: 165.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 12.0 volts power source Time Rating Per Chacteristic: 35.00 nanoseconds delay Memory Device Type: Pal Test Data Document:	1.2 watts
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Inclosure Configuration:  Dual-in-line  Output Logic Form:  Transistor-transistor logic  Input Circuit Pattern:  20 input  Case Outline Source And Designator:  D-9 mil-m-38510  Current Rating Per Characteristic:  165.00 milliamperes reverse current, dc absolute  Terminal Surface Treatment:  Solder  Product Name:  And-or invert gate array  Voltage Rating And Type Per Characteristic:  -0.5 volts power source and 12.0 volts power source  Time Rating Per Chacteristic:  35.00 nanoseconds delay  Memory Device Type:  Pal  Test Data Document:	Inclosure Material:
Dual-in-line  Output Logic Form: Transistor-transistor logic Input Circuit Pattern: 20 input  Case Outline Source And Designator: D-9 mil-m-38510  Current Rating Per Characteristic: 165.00 milliamperes reverse current, dc absolute  Terminal Surface Treatment: Solder  Product Name: And-or invert gate array  Voltage Rating And Type Per Characteristic: -0.5 volts power source and 12.0 volts power source  Time Rating Per Chacteristic: 35.00 nanoseconds delay  Memory Device Type: Pal  Test Data Document:	Ceramic
Output Logic Form: Transistor-transistor logic Input Circuit Pattern: 20 input Case Outline Source And Designator: D-9 mil-m-38510 Current Rating Per Characteristic: 165.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 12.0 volts power source Time Rating Per Chacteristic: 35.00 nanoseconds delay Memory Device Type: Pal Test Data Document:	Inclosure Configuration:
Transistor-transistor logic  Input Circuit Pattern: 20 input  Case Outline Source And Designator: D-9 mil-m-38510  Current Rating Per Characteristic: 165.00 milliamperes reverse current, dc absolute  Terminal Surface Treatment: Solder  Product Name: And-or invert gate array  Voltage Rating And Type Per Characteristic: -0.5 volts power source and 12.0 volts power source  Time Rating Per Chacteristic: 35.00 nanoseconds delay  Memory Device Type: Pal  Test Data Document:	Dual-in-line
Input Circuit Pattern:  20 input  Case Outline Source And Designator:  D-9 mil-m-38510  Current Rating Per Characteristic:  165.00 milliamperes reverse current, dc absolute  Terminal Surface Treatment:  Solder  Product Name:  And-or invert gate array  Voltage Rating And Type Per Characteristic:  -0.5 volts power source and 12.0 volts power source  Time Rating Per Chacteristic:  35.00 nanoseconds delay  Memory Device Type:  Pal  Test Data Document:	Output Logic Form:
Case Outline Source And Designator:  D-9 mil-m-38510  Current Rating Per Characteristic: 165.00 milliamperes reverse current, dc absolute  Terminal Surface Treatment: Solder  Product Name: And-or invert gate array  Voltage Rating And Type Per Characteristic: -0.5 volts power source and 12.0 volts power source  Time Rating Per Chacteristic: 35.00 nanoseconds delay  Memory Device Type: Pal  Test Data Document:	Transistor-transistor logic
Case Outline Source And Designator:  D-9 mil-m-38510  Current Rating Per Characteristic:  165.00 milliamperes reverse current, dc absolute  Terminal Surface Treatment:  Solder  Product Name:  And-or invert gate array  Voltage Rating And Type Per Characteristic:  -0.5 volts power source and 12.0 volts power source  Time Rating Per Chacteristic:  35.00 nanoseconds delay  Memory Device Type:  Pal  Test Data Document:	Input Circuit Pattern:
D-9 mil-m-38510  Current Rating Per Characteristic:  165.00 milliamperes reverse current, dc absolute  Terminal Surface Treatment:  Solder  Product Name:  And-or invert gate array  Voltage Rating And Type Per Characteristic:  -0.5 volts power source and 12.0 volts power source  Time Rating Per Chacteristic:  35.00 nanoseconds delay  Memory Device Type:  Pal  Test Data Document:	20 input
Current Rating Per Characteristic:  165.00 milliamperes reverse current, dc absolute  Terminal Surface Treatment:  Solder  Product Name: And-or invert gate array  Voltage Rating And Type Per Characteristic: -0.5 volts power source and 12.0 volts power source  Time Rating Per Chacteristic:  35.00 nanoseconds delay  Memory Device Type: Pal  Test Data Document:	Case Outline Source And Designator:
165.00 milliamperes reverse current, dc absolute  Terminal Surface Treatment: Solder  Product Name: And-or invert gate array  Voltage Rating And Type Per Characteristic: -0.5 volts power source and 12.0 volts power source  Time Rating Per Chacteristic: 35.00 nanoseconds delay  Memory Device Type: Pal  Test Data Document:	D-9 mil-m-38510
Terminal Surface Treatment: Solder Product Name: And-or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 12.0 volts power source Time Rating Per Chacteristic: 35.00 nanoseconds delay Memory Device Type: Pal Test Data Document:	Current Rating Per Characteristic:
Solder  Product Name: And-or invert gate array  Voltage Rating And Type Per Characteristic: -0.5 volts power source and 12.0 volts power source  Time Rating Per Chacteristic: 35.00 nanoseconds delay  Memory Device Type: Pal  Test Data Document:	165.00 milliamperes reverse current, dc absolute
Product Name: And-or invert gate array  Voltage Rating And Type Per Characteristic: -0.5 volts power source and 12.0 volts power source  Time Rating Per Chacteristic: 35.00 nanoseconds delay  Memory Device Type: Pal  Test Data Document:	Terminal Surface Treatment:
And-or invert gate array  Voltage Rating And Type Per Characteristic:  -0.5 volts power source and 12.0 volts power source  Time Rating Per Chacteristic:  35.00 nanoseconds delay  Memory Device Type:  Pal  Test Data Document:	Solder
Voltage Rating And Type Per Characteristic:  -0.5 volts power source and 12.0 volts power source  Time Rating Per Chacteristic:  35.00 nanoseconds delay  Memory Device Type:  Pal  Test Data Document:	Product Name:
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35.00 nanoseconds delay  Memory Device Type: Pal  Test Data Document:	-0.5 volts power source and 12.0 volts power source
Memory Device Type: Pal Test Data Document:	Time Rating Per Chacteristic:
Pal  Test Data Document:	35.00 nanoseconds delay
Test Data Document:	Memory Device Type:
	Pal
96906-mil-std-883 standard (includes industry or association standards individual manufactureer standards, etc.)	Test Data Document:
11111 113 333 316.116.116.116.116.116.116.116.116.116.	96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.)

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T	erm	inal	Type	Δnd	Ou	antity	,.
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24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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